

## NCE Automotive N-Channel Super Trench II Power MOSFET

### Description

The NCEAP028N85D uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

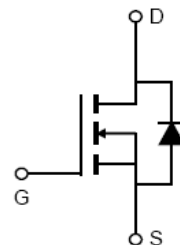
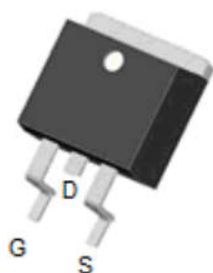
### Application

- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

- $V_{DS}=85V, I_D=220A$   
 $R_{DS(ON)}=2.4m\Omega$ , typical @  $V_{GS}=10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175°C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100%  $\Delta V_{ds}$  tested
- **AEC-Q101 qualified**

TO-263



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP028N85D	NCEAP028N85D	TO-263	-	-	-

### Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	85	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	220	A
Drain Current-Continuous( $T_c=100^\circ\text{C}$ )	$I_D(100^\circ\text{C})$	150	A
Pulsed Drain Current	$I_{DM}$	800	A
Maximum Power Dissipation	$P_D$	245	W
Derating factor		1.63	W/°C
Single pulse avalanche energy (Note 1)	$E_{AS}$	1767	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.61	°C/W
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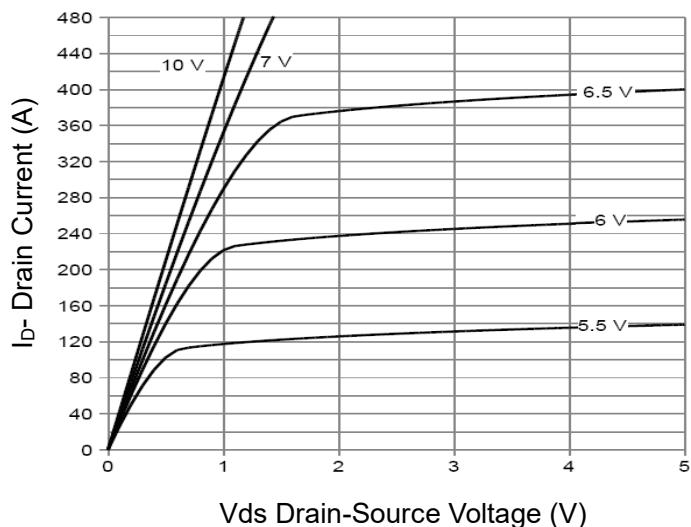
**Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	85	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =85V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	2.4	2.8	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	-	200	-	S
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, F=1.0MHz	-	7680	-	pF
Output Capacitance	C <sub>oss</sub>		-	1472	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	60	-	pF
Switching Characteristics <sup>(Note 2)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =40V, I <sub>D</sub> =20A V <sub>GS</sub> =10V, R <sub>G</sub> =1.6Ω	-	25	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	15	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	52	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	17	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =40V, I <sub>D</sub> =100A, V <sub>GS</sub> =10V	-	124	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	37	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	33	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current	I <sub>S</sub>		-	-	220	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 100A	-	98	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100A/μs	-	280	-	nC

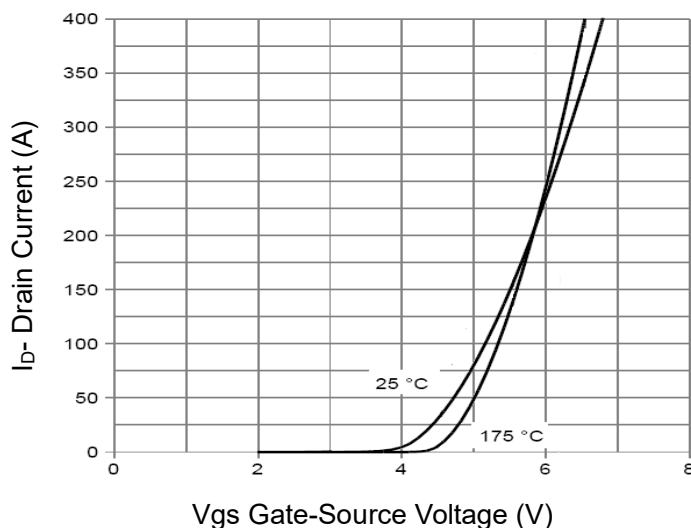
**Notes:**

1. EAS condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=40V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=175° C. The SOA curve provides a single pulse rating.

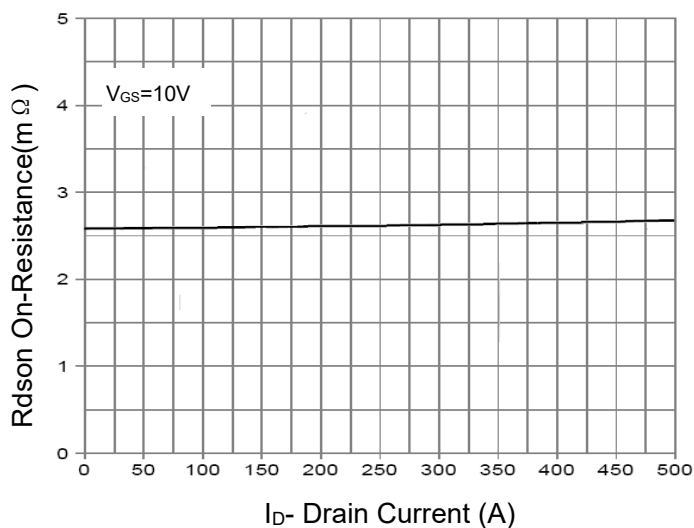
## Typical Electrical and Thermal Characteristics



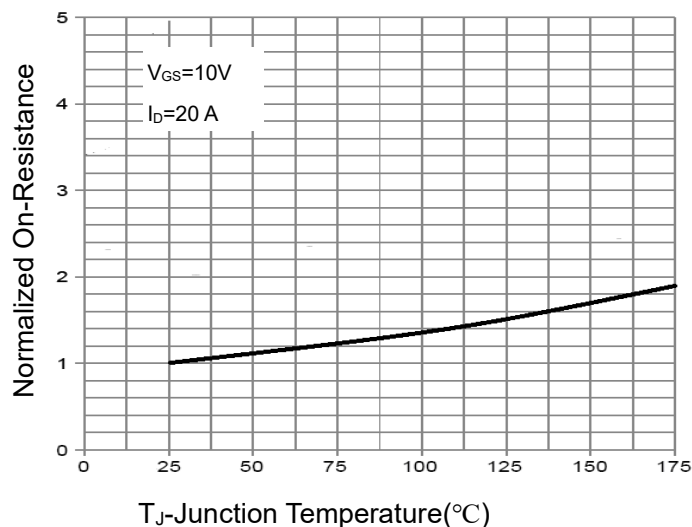
**Figure 1 Output Characteristics**



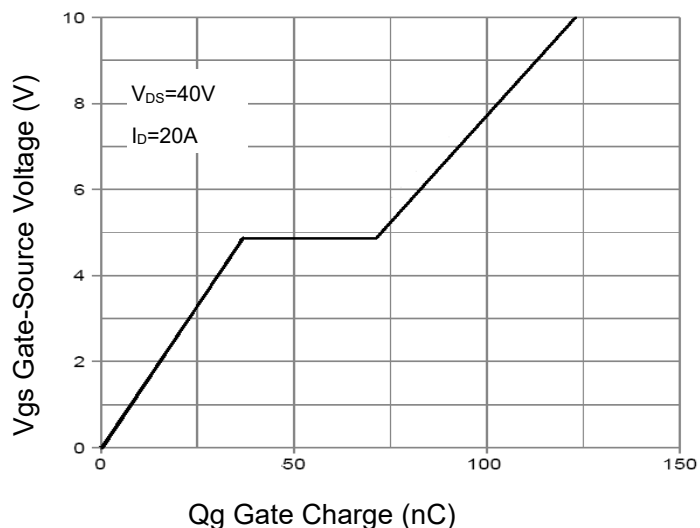
**Figure 2 Transfer Characteristics**



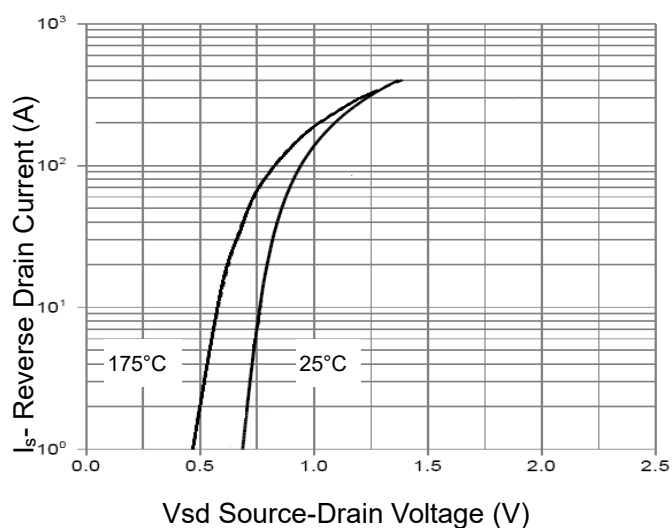
**Figure 3 Rdson- Drain Current**



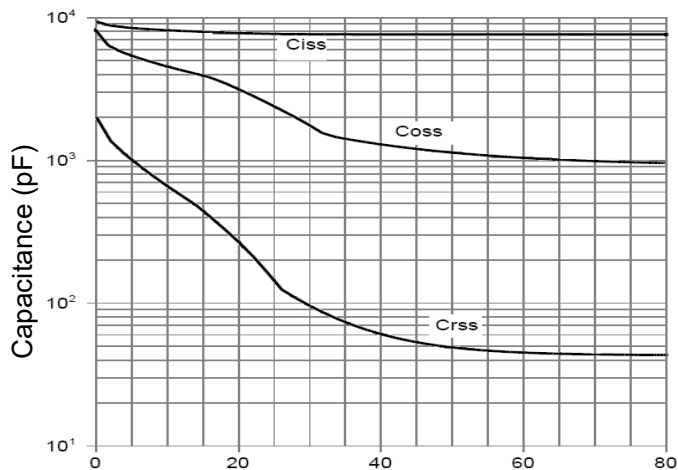
**Figure 4 Rdson-Junction Temperature**



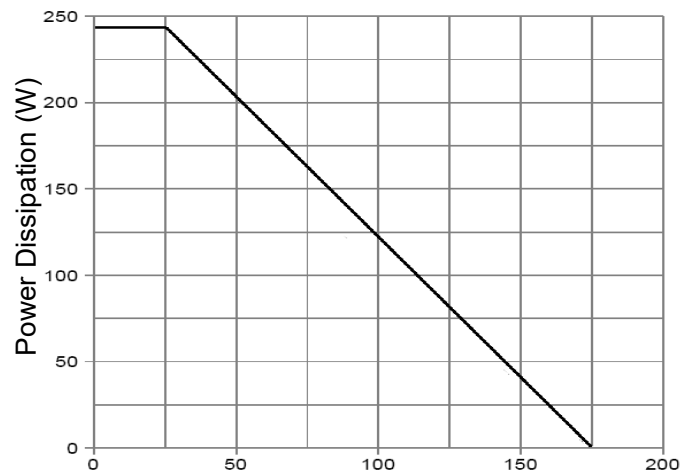
**Figure 5 Gate Charge**



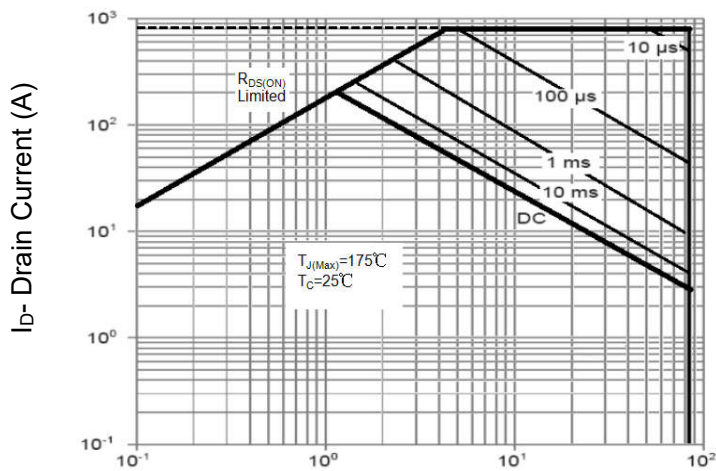
**Figure 6 Source- Drain Diode Forward**



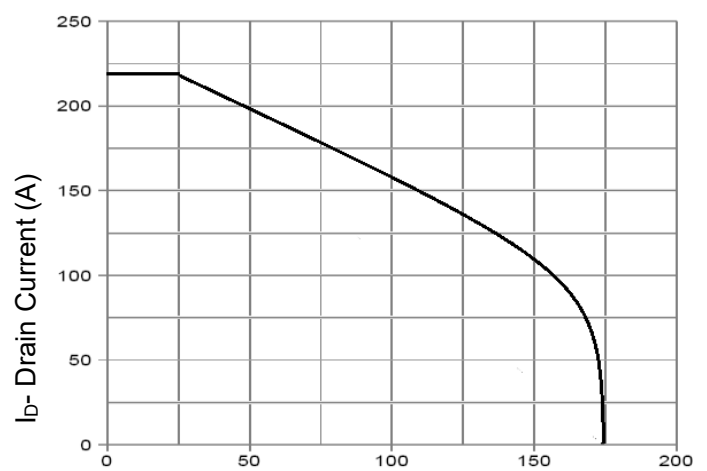
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



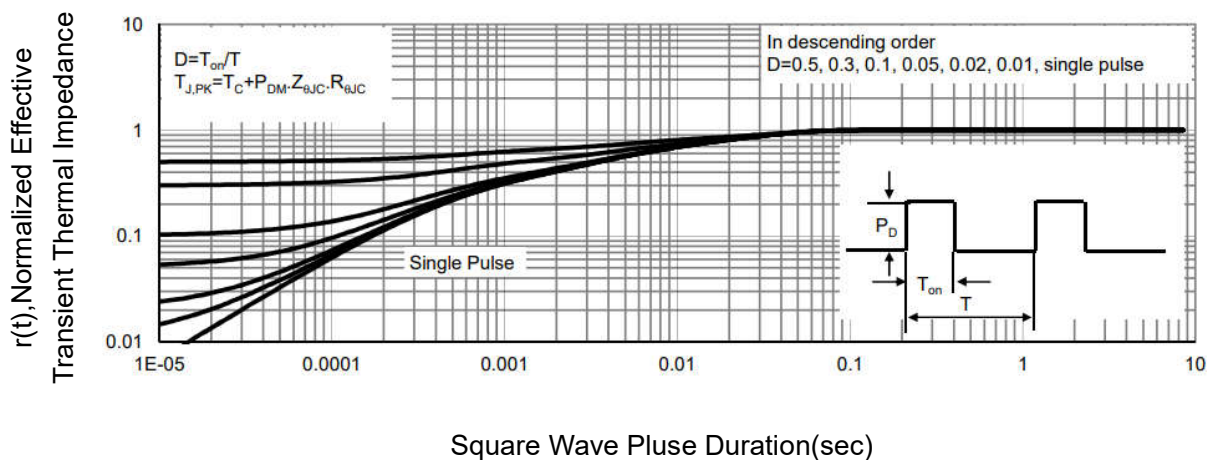
TJ-Junction Temperature(°C)  
**Figure 9 Power De-rating**



Vds Drain-Source Voltage (V) (Note 3)  
**Figure 8 Safe Operation Area**

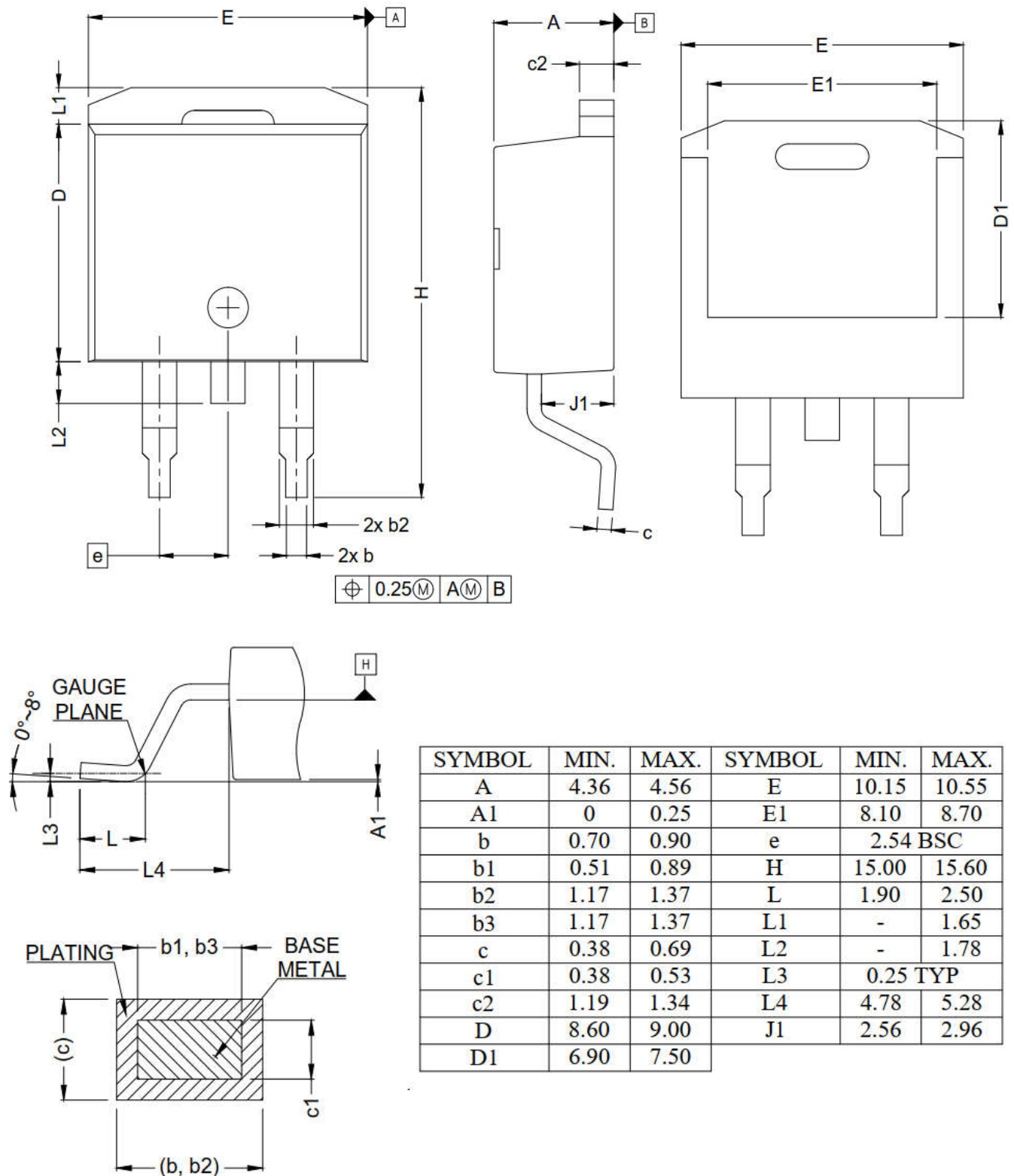


TJ-Junction Temperature (°C)  
**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## TO-263-2L Package Information



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